Proceedings of the 15th International Conference on Defects Recognition, Imaging and Physics in Semiconductors

Warsaw, Poland, September 15–19, 2013

Editor of the Proceedings:

Janusz Kaniewski

WARSAW

POLISH ACADEMY OF SCIENCES
INSTITUTE OF PHYSICS

Conference Chairpersons:

Maciej Bugajski, *Institute of Electron Technology, Poland*
Rajmund Bacewicz, *Warsaw University of Technology, Poland*

International Steering Committee:

Takashi Sekiguchi (ISC chair), *Japan*
Jean-Pierre Fillard (Honorary Member), *France*
Michio Tajima, *Japan*
Martina Baeumler, *Germany*
Peder Bergman, *Sweden*
Maciej Bugajski, *Poland*
Piotr Edelman, *USA*
Cesare Frigeri, *Italy*
Juan Jimenez, *Spain*
Junyong Kang, *China*
Jean-Pierre Landesman, *France*
Paul Montgomery, *France*
Michelle Moram, *United Kingdom*
Lucia Nasi, *Italy*
Hidekazu Tsuchida, *Japan*
Jens W. Tomm, *Germany*
Jan Weyher, *Poland*
Deren Yang, *China*
Ute Zeimer, *Germany*

Organizing Committee:

Anna Wójcik-Jedlińska — *Secretary*
Emilia Pruszyńska-Karbownik
Ewa Papis-Polakowska — *Exhibition*

Preface

The present issue of *Acta Physica Polonica A* contains selected papers presented at the 15th International Conference on Defects Recognition, Imaging and Physics in Semiconductors, *DRIP XV*. The conference was held in Warsaw, Poland, in the five-day period from September 15th to 19th, 2013. It was accompanied by exhibition of scientific instruments. The Conference was organized jointly by the Institute of Electron Technology and Warsaw University of Technology.

International Conference on Defects Recognition, Imaging and Physics in Semiconductors DRIP was established in France by Professor J. P. Fillard in 1985 and since that time 15 DRIP conferences have been held in Europe, America, and Asia. For almost 30 years, DRIP has focused on all aspects of defects in semiconductors including point, line, planar and volume defects studied by a variety of techniques. This comprehensive approach has allowed for a discussion of the multifaceted effects of growth, processing and device fabrication and their interrelationships.

The last Conference, in Warsaw, was attended by almost 100 participants. The presentations included 8 invited talks, 50 contributed talks and posters and 5 talks on modern scientific equipment produced by well-recognized companies. All papers in this issue were reviewed by distinguished colleagues after the conference.

Last section of proceedings contains articles presenting in depth the experimental methods utilized by equipment exhibited during the Conference. This section could be arranged thanks to the hard work of exhibitors. We greatly appreciate their contribution.

We would like to thank all members of the Program Committee for their work in the selection process of invited and contributed papers and setting up the scientific program of the Conference.

The next, 16th Conference on Defects Recognition, Imaging and Physics in Semiconductors will be held in 2015 in China.

I wish also success to the future organizers of conferences in the DRIP series.

Janusz Kaniewski
Warsaw, April 2014